

**N - CHANNEL ENHANCEMENT MODE
 POWER MOS TRANSISTOR**

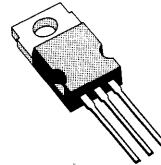
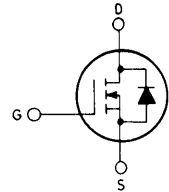
TYPE	V _{DSS}	R _{DS(on)}	I _D
BUZ76A	400 V	2.5 Ω	2.6 A

- HIGH VOLTAGE - FOR OFF-LINE APPLICATIONS
- ULTRA FAST SWITCHING
- EASY DRIVE - FOR REDUCED COST AND SIZE

INDUSTRIAL APPLICATIONS:

- ELECTRONIC LAMP BALLAST
- DC SWITCH

N - channel enhancement mode POWER MOS field effect transistor. Easy drive and very fast switching times make this POWER MOS transistor ideal for high speed switching applications. Applications include off-line use, constant current source, ultrasonic equipment and switching power supply start-up circuits.


TO-220
**INTERNAL SCHEMATIC
 DIAGRAM**

ABSOLUTE MAXIMUM RATINGS

V _{DS}	Drain-source voltage (V _{GS} = 0)	400	V
V _{DGR}	Drain-gate voltage (R _{GS} = 20 KΩ)	400	V
V _{GS}	Gate-source voltage	±20	V
I _D	Drain current (continuous) T _c = 30°C	2.6	A
I _{DM}	Drain current (pulsed)	10	A
P _{tot}	Total dissipation at T _c < 25°C	40	W
T _{stg}	Storage temperature	-55 to 150	°C
T _j	Max. operating junction temperature	150	°C
	DIN humidity category (DIN 40040)	E	
	IEC climatic category (DIN IEC 68-1)	55/150/56	

THERMAL DATA

$R_{thj - case}$	Thermal resistance junction-case	max	3.1	°C/W
$R_{thj - amb}$	Thermal resistance junction-ambient	max	75	°C/W

ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$ unless otherwise specified)

Parameters	Test Conditions	Min.	Typ.	Max.	Unit
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OFF

$V_{(BR) DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu\text{A}$	$V_{GS} = 0$	400		V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$	$T_j = 125^\circ\text{C}$		250 1000	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 \text{ V}$			± 100	nA

ON

$V_{GS (th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$	$I_D = 1 \text{ mA}$	2.1		4	V
$R_{DS (on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}$	$I_D = 1.5 \text{ A}$			2.5	Ω

DYNAMIC

g_{fs}	Forward transconductance	$V_{DS} = 25 \text{ V}$	$I_D = 1.5 \text{ A}$	0.8			mho
C_{iss}	Input capacitance	$V_{DS} = 25 \text{ V}$ $V_{GS} = 0$	$f = 1 \text{ MHz}$			500	pF
C_{oss}	Output capacitance					80	pF
C_{rss}	Reverse transfer capacitance					60	pF

SWITCHING

$t_{d (on)}$	Turn-on time	$V_{DD} = 30 \text{ V}$	$I_D = 2.4 \text{ A}$			20	ns
t_r	Rise time	$R_{GS} = 50 \Omega$	$V_{GS} = 10 \text{ V}$			60	ns
$t_{d (off)}$	Turn-off delay time					65	ns
t_f	Fall time					40	ns

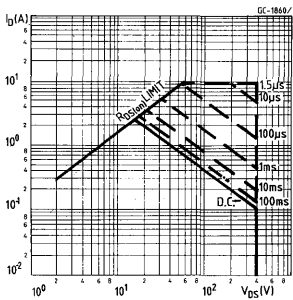
ELECTRICAL CHARACTERISTICS (Continued)

Parameters	Test Conditions	Min.	Typ.	Max.	Unit
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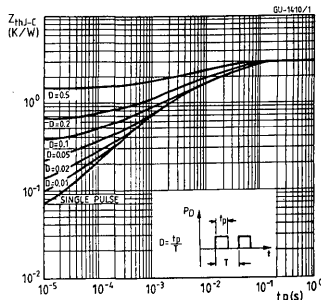
SOURCE DRAIN DIODE

I_{SD} I_{SDM}	Source-drain current Source-drain current (pulsed)	$T_c = 25^\circ\text{C}$		2.6 10	A A
V_{SD}	Forward on voltage	$I_{SD} = 5.2\text{ A}$	$V_{GS} = 0$	1.4	V
t_{rr}	Reverse recovery time			300	ns
Q_{rr}	Reverse recovered charge	$I_{SD} = 2.6\text{ A}$	$di/dt = 100\text{A}/\mu\text{s}$	2.5	μC

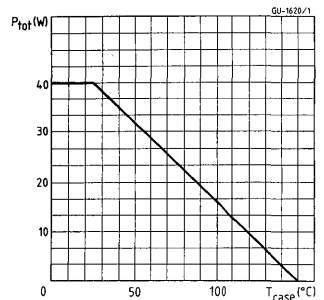
Safe operating areas



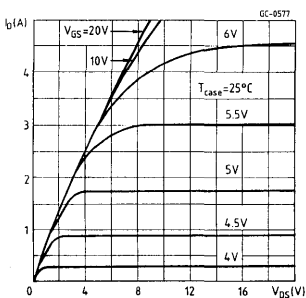
Thermal impedance



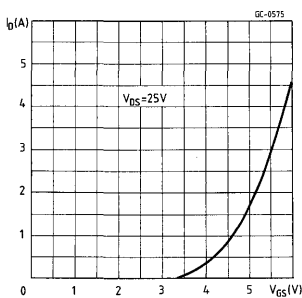
Derating curve



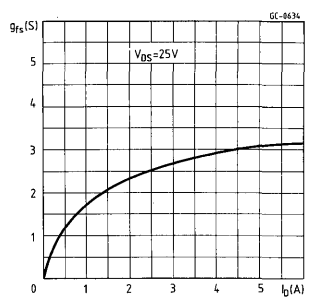
Output characteristics



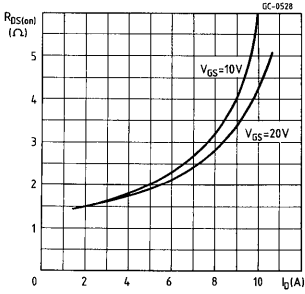
Transfer characteristics



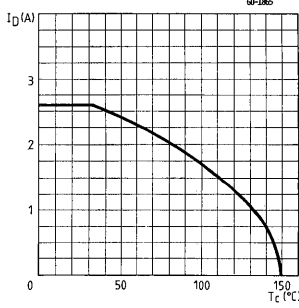
Transconductance



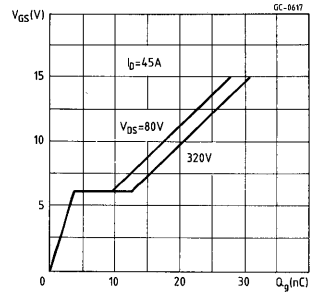
Static drain-source on resistance



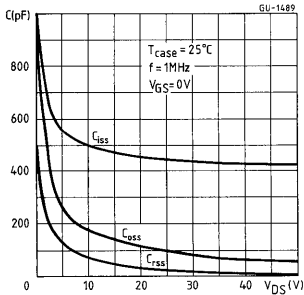
Maximum drain current vs temperature



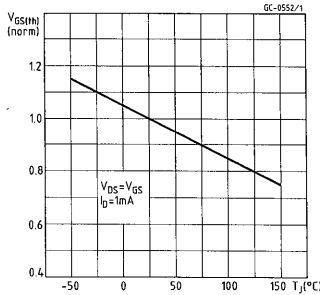
Gate charge vs gate-source voltage



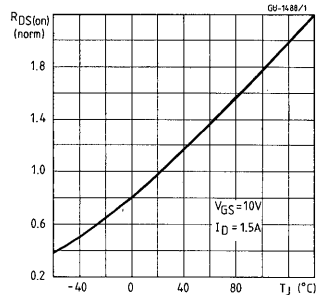
Capacitance variation



Gate threshold voltage vs temperature



Drain-source on resistance vs temperature



Source-drain diode forward characteristics

